

L03AUT1006

List

List.....	1
Package outline.....	2
Features.....	2
Applications.....	2
Mechanical data.....	2
Maximum ratings	2
Electrical characteristics.....	2
Rating and characteristic curves.....	3
Electrical parameters.....	4
Pinning information.....	4
Marking.....	4
Suggested solder pad layout.....	4
Packing information.....	5
Reel packing.....	6
Suggested thermal profiles for soldering processes.....	6
High reliability test capabilities.....	7

L03AUT1006

Low Capacitance TVS Uni-Directional For ESD Protection Diode 3.3V

Features

- Protects one data line
- Low capacitance : 1.5pF (Typical)
- Low leakage current : 0.01 μ A @V_{RWM} (Typical)
- Low operating and clamping voltage
- Each I/O pin can withstand over 1000 ESD Strikes for $\pm$ 8kV contact discharge
- Provide transient protection:
 - IEC 61000-4-2 (ESD) $\pm$ 30kV(Air)
 - $\pm$ 30kV(Contact)
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Surge) 10A (8/20 μ s)
- Lead-free parts meet RoHS requirements
- Suffix "-H" indicates Halogen-free parts, ex.L03AUT1006-H

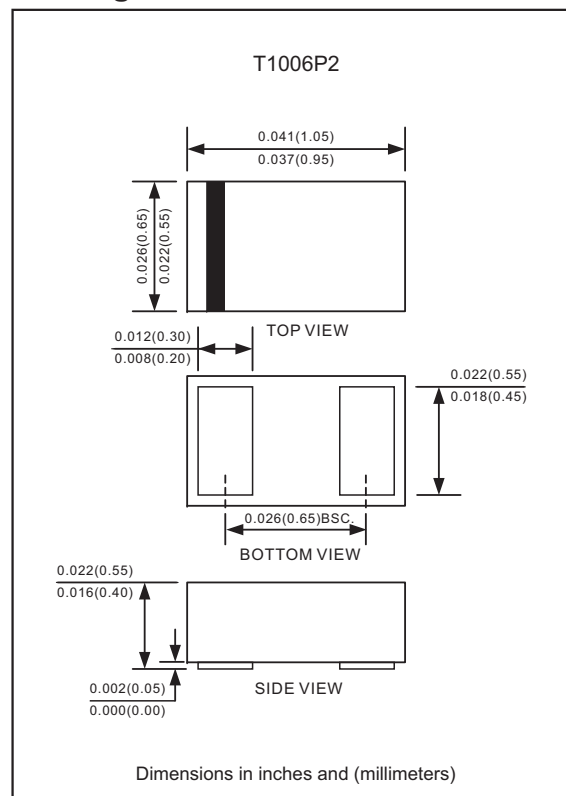
Applications

- Desktops, servers and notebooks
- Cellular phones
- Portable instruments
- Analog inputs

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic,T1006P2
- Mounting Position : Any
- Weight : Approximated 1.00 mg

Package outline



Maximum ratings (at T_A=25°C unless otherwise noted)

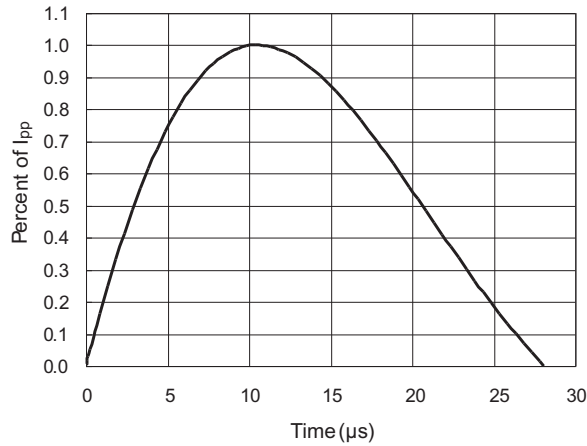
Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Air)	V _{ESD}	$\pm$ 30	kV
ESD per IEC 61000-4-2 (Contact)		$\pm$ 30	
Peak pulse current (8/20 μ s)	I _{PP}	10	A
Peak pulse power (8/20 μ s)	P _{PP}	100	W
Operating temperature range	T _{OPT}	-45 to +85	°C
Storage temperature range	T _{STG}	-55 to +150	°C

Electrical Characteristics (at T_A=25°C unless otherwise noted)

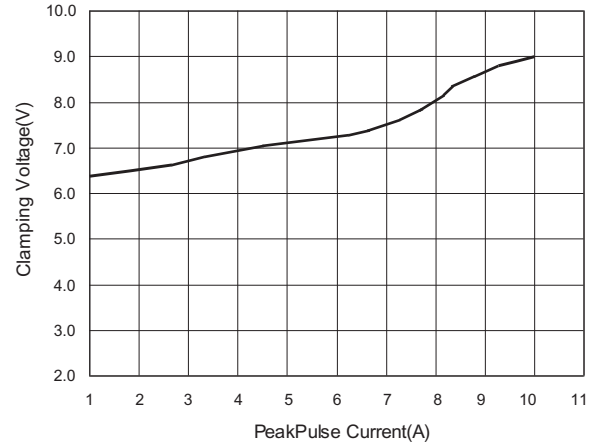
Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	Unit
Nominal reverse working voltage		V _{RWM}			3.3	V
Trigger voltage	I _{t1} =1 μ A	V _{t1}	4.0		7.0	V
Holding voltage	I _h =20mA	V _h	3.0		5.0	V
Reverse leakage current	V _{RWM} =3.3V, T _J = 25°C	I _R		0.01	0.1	μ A
Clamping voltage	I _{PP} =1A, tp=8/20 μ s	V _C			6.5	V
	I _{PP} =10A, tp=8/20 μ s				10.0	
Parasitic capacitance	V _R =3.3V, f=1MHz	C _J		1.5	2.0	pF

Rating and characteristic curves(L03AUT1006)

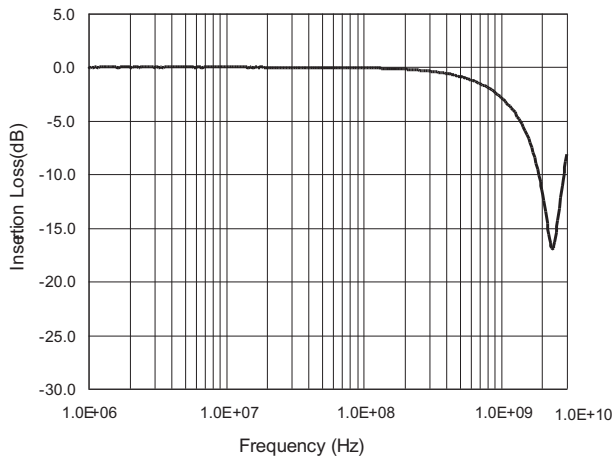
8/20 μ s Pulse Waveform



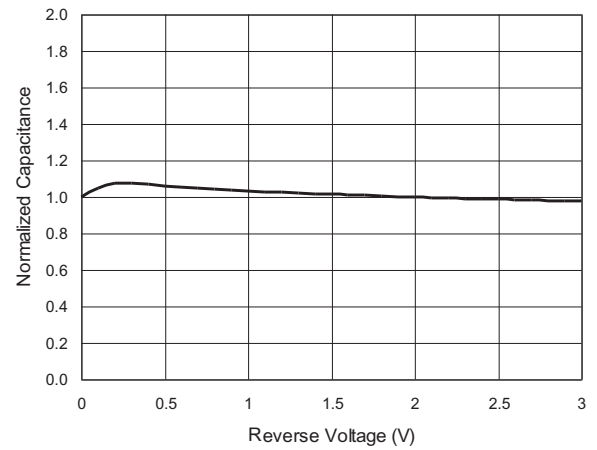
Clamping Voltage V_C vs. Current I_{PP}



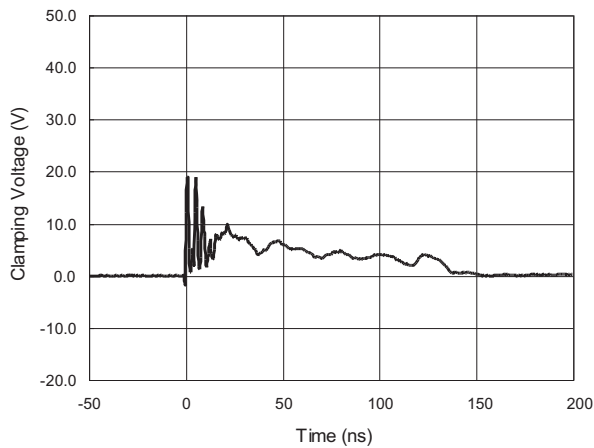
Insertion Loss S21



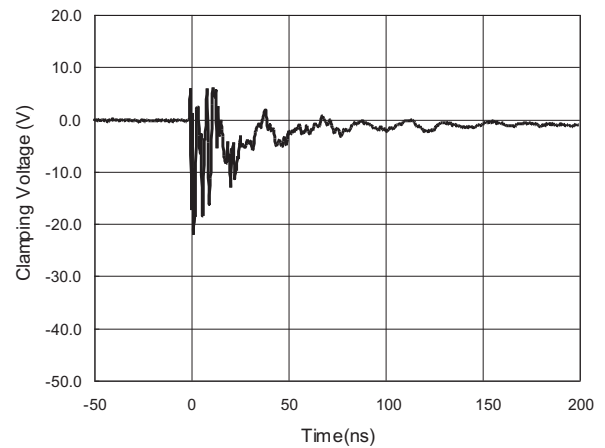
Normalized Capacitance vs. Voltage



ESD Clamping of I/O to GND
(+8kV Contact per IEC 61000-4-2)



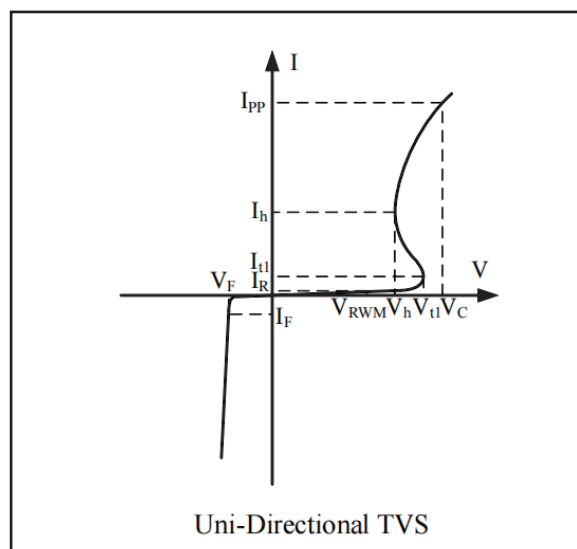
ESD Clamping of I/O to GND
(-8kV Contact per IEC 61000-4-2)



L03AUT1006

Electrical Parameters ($T_A=25^{\circ}\text{C}$)

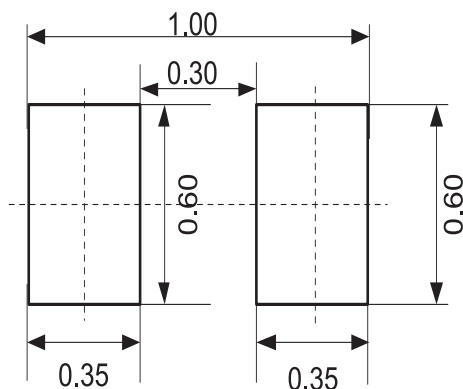
Symbol	Parameter
V_{RWM}	Nominal reverse working voltage
I_R	Reverse leakage current @ V_{RWM}
V_{t1}	Trigger voltage
I_{t1}	Trigger current @ V_{t1}
V_h	Holding voltage
I_h	Holding current @ V_h
V_c	Clamping voltage @ I_{PP}
V_{CR}	Reverse clamping voltage @ I_{PP}
I_{PP}	Maximum peak pulse current
C_{ESD}	Parasitic capacitance



Pinning information

Pin	Marking Code	Symbol

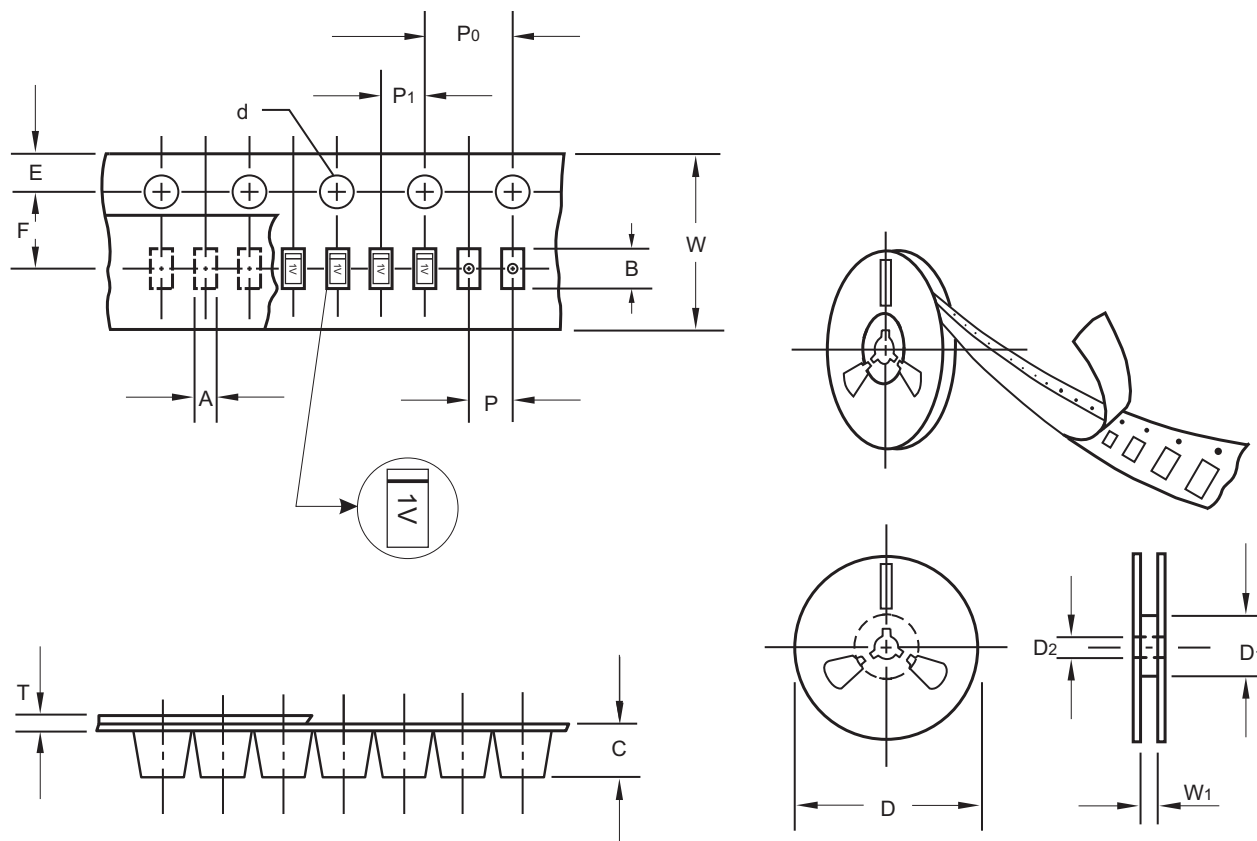
Suggested solder pad layout



Dimensions in millimeters

L03AUT1006

Packing information



unit:mm

Item	Symbol	Tolerance	T1006P2
Carrier width	A	0.1	0.66
Carrier length	B	0.1	1.15
Carrier depth	C	0.1	0.66
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	55.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	2.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	9.50

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

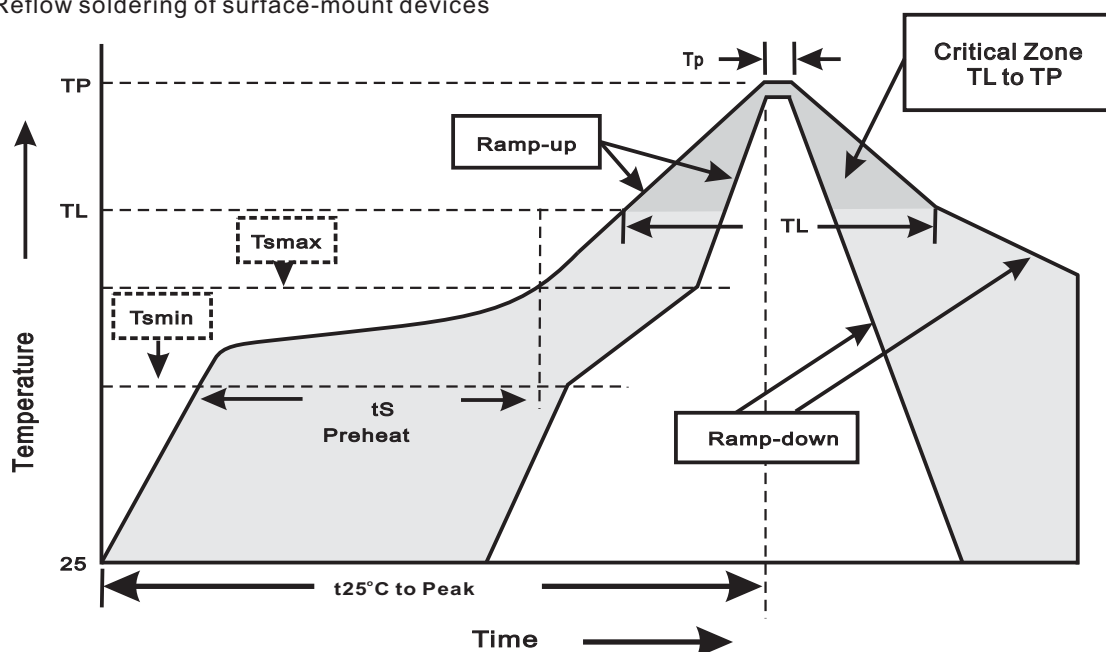
L03AUT1006

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
T1006P2	7"	10,000	2.0	100,000	183*123*183	178	382*257*387	800,000	15.0

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{sm}) -Temperature Max(T _{smx}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{smx} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

L03AUT1006

High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at $260 \pm 5^{\circ}\text{C}$ for $10 \pm 2\text{sec.}$	MIL-STD-750D METHOD-2031
2. Solderability	at $245 \pm 5^{\circ}\text{C}$ for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_{\text{BR}} = V_{\text{BR MIN}} * 80\%$ at $T_j = 85^{\circ}\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Pressure Cooker	$15P_{\text{SIG}}$ at $T_A = 121^{\circ}\text{C}$ for 4 hrs.	JESD22-A102
5. Temperature Cycling	-55°C to $+125^{\circ}\text{C}$ dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
6. Humidity	at $T_A = 85^{\circ}\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
7. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031